

This cross-sectional view shows a semiconductor device 100. It features a substrate 1 with a thin layer 2 on top. A stack of layers 3 through 11 is positioned above layer 2. Layer 3 is a thick region, while layers 4 through 11 are thinner. On top of this stack is a layer 9, which includes a protrusion 9A. To the right of the main stack, there is another structure 10 with protrusions 10A. The layers are distinguished by different hatching patterns.

Fig. 2B is a cross-sectional view of the semiconductor device. It shows a central channel 12A with a top layer of Au and a bottom layer of Ni. The channel is flanked by side contacts 12, which are formed on a substrate 72. The side contacts 12 are shown with a cross-hatched pattern, indicating a different material or structure. The channel 12A is shown with a dashed line, indicating its internal structure or a specific layer.

FIG. 3

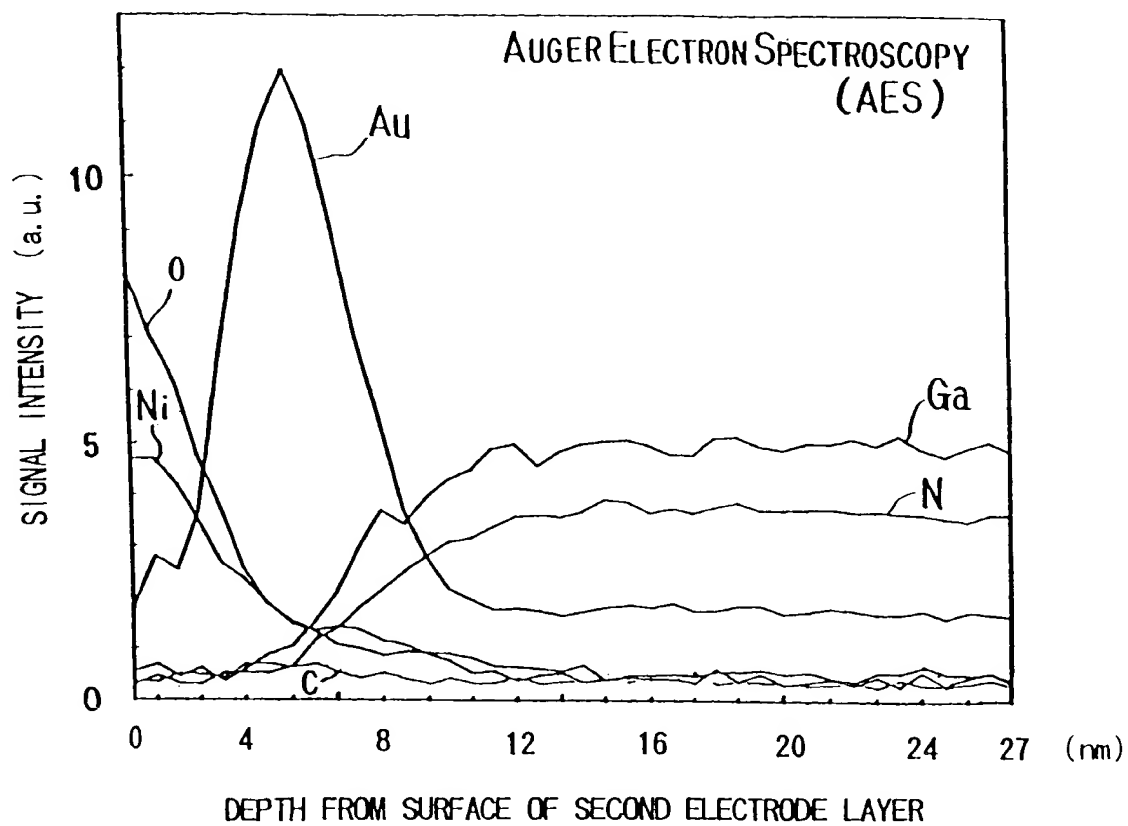


FIG. 4

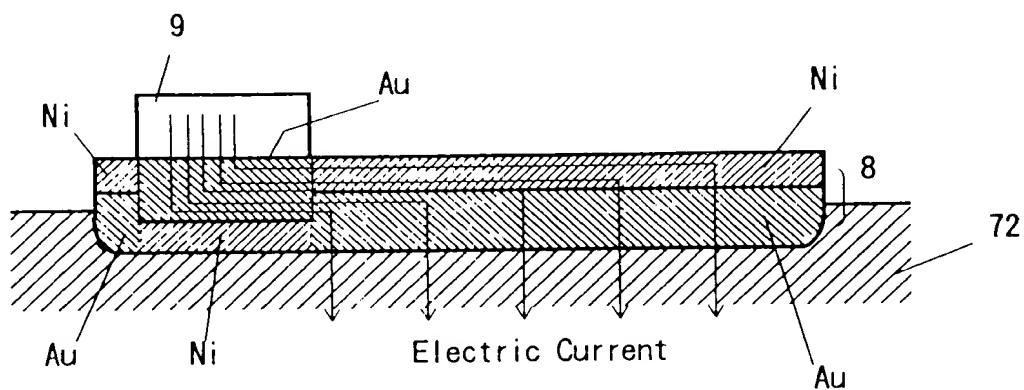


FIG. 5A PRIOR ART

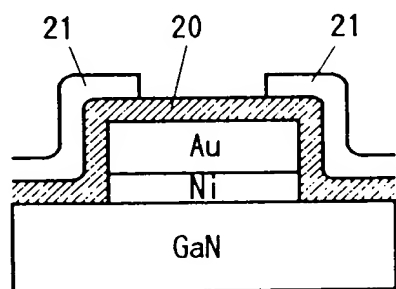


FIG. 5B PRIOR ART

